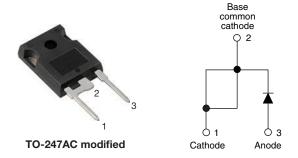
VS-30EPH06PbF, VS-30EPH06-N3

Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt®



PRODUCT SUMMARY								
Package	TO-247AC modified (2 pins)							
I _{F(AV)}	30 A							
V_{R}	600 V							
V _F at I _F	1.34 V							
t _{rr} typ.	See Recovery table							
T _J max.	175 °C							
Diode variation	Single die							

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Single diode device
- Designed and qualified according to JEDEC®-JESD 47







RoHS COMPLIANT

HALOGEN FREE Available

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V_{RRM}		600	V					
Average rectified forward current	I _{F(AV)}	T _C = 116 °C	30	۸					
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	300	Α					
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	.,				
Forward voltage	V _F	I _F = 30 A	-	2.0	2.6	V				
		I _F = 30 A, T _J = 150 °C	-	1.34	1.75					
Reverse leakage current	I _R	$V_R = V_R$ rated	-	0.3	50					
		$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	60	500	μΑ				
Junction capacitance	C _T	V _R = 600 V	-	33	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	3.5	-	nH				



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
		$I_F = 1.0 \text{ A}, dI_F/dt =$	-	28	35					
Reverse recovery time	t _{rr}	T _J = 25 °C		-	31	-	ns			
		T _J = 125 °C	$I_F = 30 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 200 \text{ V}$	-	77	-				
Dook wasayan ayanant	I _{RRM}	T _J = 25 °C		-	3.5	-	۸			
Peak recovery current		T _J = 125 °C		-	7.7	-	A			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	65	-	20			
		T _J = 125 °C		-	345	-	nC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction to case per leg	R _{thJC}		-	0.5	0.9					
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.4	-					
Weight			-	6.0	-	g				
Weight			-	0.22	-	OZ.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC modified		30EPH06						

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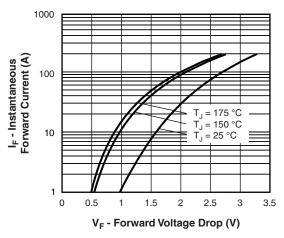


Fig. 1 - Typical Forward Voltage Drop Characteristics

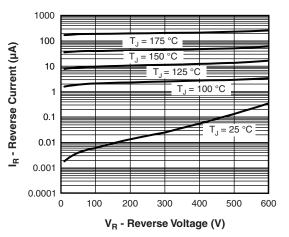


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

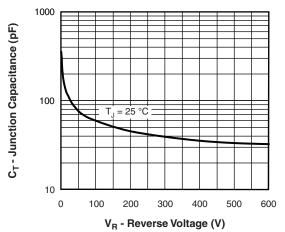


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

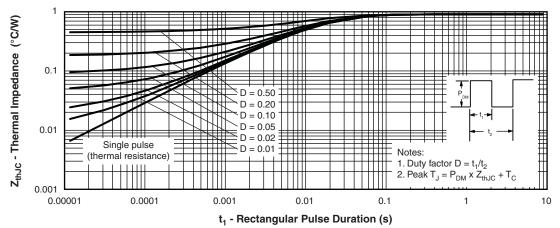


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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Allowable Case Temperature (°C)

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180 160 140 Square wave (D = 0.50) Rated V_R applied 100 See note (1) 80 0 5 10 15 20 25 30 35 40 45 I_{F(AV)} - Average Forward Current (A)

Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

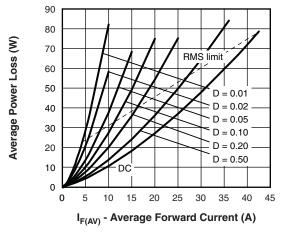


Fig. 6 - Forward Power Loss Characteristics

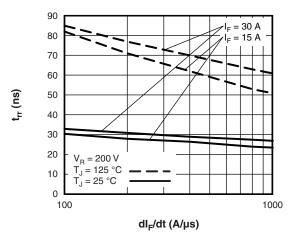


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

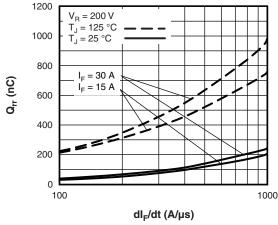


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at } (I_{F(AV)}/D) \ \text{(see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \ \text{(1 - D)}; \ I_R \ \text{at } V_{R1} = \text{Rated } V_R \\ \end{array}$

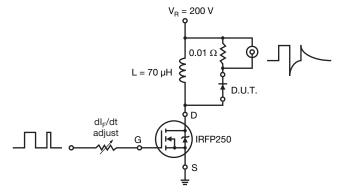
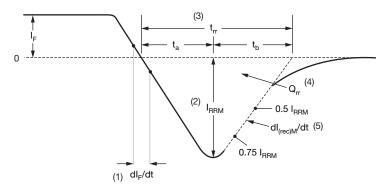


Fig. 9 - Reverse Recovery Parameter Test Circuit

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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

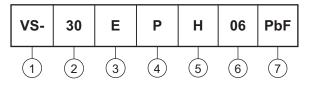
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- 2 Current rating (30 = 30 A)
- Circuit configuration:

E = single diode

4 - Package:

P = TO-247AC modified

5 - H = hyperfast recovery

6 - Voltage rating (06 = 600 V)

7 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

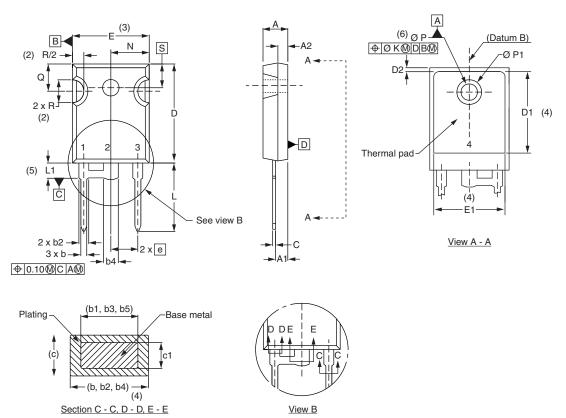
ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-30EPH06PbF	25	500	Antistatic plastic tube						
VS-30EPH06-N3	25	500	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95541						
Dout modeling information	TO-247AC modified PbF	www.vishay.com/doc?95255						
Part marking information	TO-247AC modified -N3	www.vishay.com/doc?95442						

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TO-247 - 50 mils L/F modified

DIMENSIONS in millimeters and inches



CVMDOL	MILLIN	MILLIMETERS		HES		INCHES		NOTES	CVMDOL	MILLIM	METERS	INC	HES	NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	OIE3	SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053			
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3		
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-			
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC			
b1	0.99	1.35	0.039	0.053			ØK	0.2	254	0.0)10			
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634			
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169			
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3			
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144			
С	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291			
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224			
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216			
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	'BSC			

Notes

- (1) Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC® outline TO-247 with exception of dimension c and Q



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Revision: 13-Jun-16 1 Document Number: 91000